

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Currently Amended) A photomask ~~having a pattern on~~ comprising:
a substrate ~~and~~ composed of a material transmitting exposing light; and
a pattern on said substrate of a light-shielding portions of a material that does
not transmit the exposing light, wherein said pattern ~~comprising~~ includes
a central pattern portion having a plurality of line patterns, ~~leaving a~~
~~predetermined distance~~ on a central portion of ~~the~~ said substrate;
an open portion where no light-shielding material is located and
surrounding said central pattern portion, and
a peripheral pattern portion located on and proximate a peripheral
portion of said substrate, ~~surrounding the central pattern open portion and having a~~
plurality of line patterns, each of the plurality of line patterns of said central pattern
portion and of said peripheral pattern portion consisting of linear portions of said
light-shielding material that are all parallel to each other.
2. (Previously Presented) The photomask according to claim 1, wherein the
line width of each of said line patterns is at least λ/NA , where λ is the wavelength of
the exposing light of an exposing apparatus used for transferring the patterns, and NA
is the numerical aperture of a projection lens of the exposing apparatus.
3. (Currently Amended) The photomask according to claim 1, wherein ~~the~~
length ~~said linear portions of said light-shielding material of said plurality of line~~
~~pattern is~~ patterns of said central pattern portions are at least 10 μm in length.

4. (Currently Amended) The photomask according to claim 1, wherein the number of said linear portions of said plurality of line patterns of said central pattern portion is 9.

Claim 5 (Cancelled).

6. (Currently Amended) The photomask according to claim-~~5~~ 1, wherein said open portion has a width equal to or larger than a threshold value, wherein the threshold value is the width of said open portion when the line width of a transferred pattern corresponding to said plurality of line-pattern patterns in said central portion becomes constant, despite widening of ~~the~~ said open portion.

Claims 7-20 (Cancelled).

21. (New) A pair of photomasks for measuring flair rate, each photomask comprising:

a substrate composed of a material transmitting exposing light; and

a pattern on said substrate of a light-shielding material that does not transmit the exposing light, wherein

each of said patterns includes

a central pattern portion having a plurality of line patterns on a central portion of said substrate,

an open portion where no light-shielding material is located and surrounding said central pattern portion, and

a peripheral pattern portion located on and proximate a peripheral portion of said substrate, surrounding the open portion and having a plurality of line patterns,

said central pattern portions of said pair of photomasks have identical configurations,

the open portions of said pair of photomasks are different in size from each other, and

said peripheral pattern portions of said pair of photomasks are different in size from each other.